

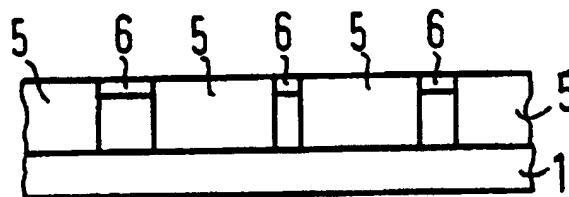


**Multilayer photoresist system.****Patent number:** EP0394738**Publication date:** 1990-10-31**Inventor:** SEZI RECAI DR-ING (DE); LEUSCHNER RAINER DR  
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G03F7/095; G03F7/20**- european:** G03F7/095; G03F7/20B; G03F7/26D; G03F7/38**Application number:** EP19900106829 19900410**Priority number(s):** DE19893913467 19890424**Also published as:** EP0394738 (A3)**Cited documents:** EP0282201 EP0251241 US3264104

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**Abstract of EP0394738**

To produce a highly resolved photoresist structure, a simplified multilayer photoresist system is proposed in which an internal mask for a second flood exposure is produced in a photoresist layer by means of a first structuring exposure at low light intensity followed by a chemical treatment. In the regions exposed first, opacity for the second exposure is achieved by treatment with a UV light absorber, while treatment with a multifunctional component produces a crosslinking of the basic polymer which renders these regions insoluble with respect to the developer used in the final development step. The process, which is in total simple to carry out, makes it possible to produce highly resolved photoresist structures with vertical edges and high aspect ratio.

**FIG 3**

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